

## **DHG10I1200PM**

preliminary

# **Sonic Fast Recovery Diode**

 $V_{RRM} = 1200 V$ 

 $I_{FAV} = 10 A$ 

 $t_{rr} = 75 \, \text{ns}$ 

High Performance Fast Recovery Diode Low Loss and Soft Recovery Single Diode

Part number

### **DHG10I1200PM**



Backside: isolated





#### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

## **Applications:**

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

## Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Base plate: Plastic overmolded tab
- Reduced weight

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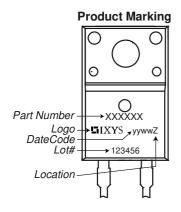
| Fast Diode        |                                     |   |                                |      | Ratings |      |      |
|-------------------|-------------------------------------|---|--------------------------------|------|---------|------|------|
| Symbol            | Definition                          | Conditions  |                                | min. | typ.    | max. | Unit |
| V <sub>RSM</sub>  | max. non-repetitive reverse blockir | ng voltage  | $T_{VJ} = 25^{\circ}C$         |      |         | 1200 | V    |
| V <sub>RRM</sub>  | max. repetitive reverse blocking vo | oltage  | $T_{VJ} = 25^{\circ}C$         |      |         | 1200 | V    |
| IR                | reverse current, drain current      | V <sub>R</sub> = 1200 V   | $T_{VJ} = 25^{\circ}C$         |      |         | 15   | μΑ   |
|                   |                                     | $V_R = 1200 V$  | $T_{VJ} = 125^{\circ}C$        |      |         | 1.2  | mΑ   |
| V <sub>F</sub>    | forward voltage drop                | I <sub>F</sub> = 10 A   | $T_{VJ} = 25^{\circ}C$         |      |         | 2.22 | V    |
|                   |                                     | $I_F = 20 A$  |                                |      |         | 2.92 | ٧    |
|                   |                                     | I <sub>F</sub> = 10 A   | T <sub>VJ</sub> = 125°C        |      |         | 2.13 | V    |
|                   |                                     | $I_F = 20 A$  |                                |      |         | 3.06 | ٧    |
| I FAV             | average forward current             | T <sub>C</sub> = 30°C   | T <sub>VJ</sub> = 150°C        |      |         | 10   | Α    |
|                   |                                     | rectangular d = 0.5   |                                |      |         |      |      |
| V <sub>F0</sub>   | threshold voltage                   |   | $T_{VJ} = 150$ °C              |      |         | 1.09 | V    |
| $\mathbf{r}_{F}$  | slope resistance                    | ss calculation only   |                                |      |         | 94   | mΩ   |
| R <sub>thJC</sub> | thermal resistance junction to case | )   |                                |      |         | 4    | K/W  |
| R <sub>thCH</sub> | thermal resistance case to heatsin  | k   |                                |      | 0.5     |      | K/W  |
| P <sub>tot</sub>  | total power dissipation             |   | $T_C = 25^{\circ}C$            |      |         | 30   | W    |
| I <sub>FSM</sub>  | max. forward surge current          | $t = 10 \text{ ms}$ ; (50 Hz), sine; $V_R = 0 \text{ V}$  | $T_{VJ} = 45^{\circ}C$         |      |         | 65   | Α    |
| CJ                | junction capacitance                | $V_R = 600  \text{V}$ f = 1 MHz   | $T_{VJ} = 25^{\circ}C$         |      | 4       |      | pF   |
| I <sub>RM</sub>   | max. reverse recovery current       |   | $T_{VJ} = 25 ^{\circ}\text{C}$ |      | 8       |      | Α    |
|                   |                                     | $I_F = 10 \text{ A}; V_R = 800 \text{ V}$   | $T_{VJ} = {}^{\circ}C$         |      | tbd     |      | Α    |
| t <sub>rr</sub>   | reverse recovery time               | $\begin{cases} I_F = 10 \text{ A; } V_R = 800 \text{ V} \\ -di_F /dt = 350 \text{ A/}\mu\text{s} \end{cases}$ | $T_{VJ} = 25 ^{\circ}\text{C}$ |      | 75      |      | ns   |
|                   | J                                   |   | $T_{VJ} = {}^{\circ}C$         |      | tbd     |      | ns   |



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| Package TO-220FP     |  |                            |   | Ratings |      |      |      |      |
|----------------------|--|----------------------------|---|---------|------|------|------|------|
| Symbol               | Definition   | Conditions                 |   |         | min. | typ. | max. | Unit |
| I <sub>RMS</sub>     | RMS current  | per terminal               |   |         |      |      | 35   | Α    |
| T <sub>VJ</sub>      | virtual junction temperature                               |                            |   |         | -55  |      | 150  | °C   |
| Top                  | operation temperature                                      |                            |   |         | -55  |      | 125  | °C   |
| T <sub>stg</sub>     | storage temperature  |                            |   |         |      |      | 150  | °C   |
| Weight               |  |                            |   |         |      | 2    |      | g    |
| M <sub>D</sub>       | mounting torque  |                            |   |         | 0.4  |      | 0.6  | Nm   |
| F <sub>c</sub>       | mounting force with clip                                   |                            |   |         | 20   |      | 60   | N    |
| $d_{\text{Spp/App}}$ | creepage distance on surface   striking distance through a | iking distance through air | terminal to terminal                    | 3.2     | 2.7  |      |      | mm   |
| $d_{Spb/Apb}$        | creepage distance on surface   striking distance through   |                            | terminal to backside                    | 2.5     | 2.5  |      |      | mm   |
| V <sub>ISOL</sub>    | isolation voltage  | t = 1 second               | 50/60 Hz, RMS; I <sub>ISOL</sub> ≤ 1 mA |         | 2500 |      |      | V    |
|                      |  | t = 1 minute               |   |         | 2100 |      |      | V    |



### Part description

D = Diode H = Sonic Fast Recovery Diode

G = extreme fast

10 = Current Rating [A]

I = Single Diode

1200 = Reverse Voltage [V] PM = TO-220ACFP (2)

| Oı | rdering | Ordering Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----|---------|-----------------|--------------------|---------------|----------|----------|
| St | tandard | DHG10I1200PM    | DHG10I1200PM       | Tube          | 50       | 503672   |

| Similar Part | Package      | Voltage class |
|--------------|--------------|---------------|
| DHG10I1200PA | TO-220AC (2) | 1200          |

| <b>Equivalent Circuits for Simulation</b> |                      |               | * on die level | $T_{VJ} = 150$ °C |
|---|----------------------|---------------|----------------|-------------------|
| $I \rightarrow V_0$                       | )—[R <sub>0</sub> ]- | Fast<br>Diode |                |                   |
| V <sub>0 max</sub>                        | threshold voltage    | 1.09          |                | V                 |
| $R_{0 \text{ max}}$                       | slope resistance *   | 91            |                | $m\Omega$         |

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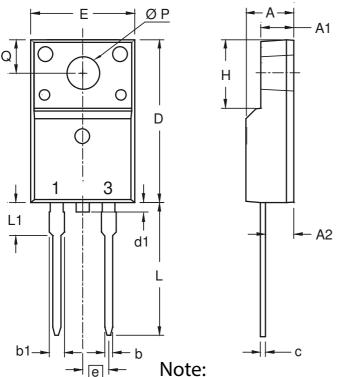


Inches



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## Outlines TO-220FP



|    | min   | max            | min   | max   |
|----|-------|----------------|-------|-------|
| Α  | 4.50  | 4.90           | 0.177 | 0.193 |
| A1 | 2.34  | 2.74           | 0.092 | 0.108 |
| A2 | 2.56  | 2.96           | 0.101 | 0.117 |
| b  | 0.70  | 0.90           | 0.028 | 0.035 |
| b1 | 1.27  | 1.47           | 0.050 | 0.058 |
| С  | 0.45  | 0.60           | 0.018 | 0.024 |
| D  | 15.67 | 16.07          | 0.617 | 0.633 |
| d1 | 0     | 1.10           | 0     | 0.043 |
| Е  | 9.96  | 10.36          | 0.392 | 0.408 |
| е  | 2.54  | 2.54 BSC 0.100 |       | BSC   |
| Н  | 6.48  | 6.88           | 0.255 | 0.271 |
| L  | 12.68 | 13.28          | 0.499 | 0.523 |
| L1 | 3.03  | 3.43           | 0.119 | 0.135 |
| ØΡ | 3.08  | 3.28           | 0.121 | 0.129 |
| Q  | 3.20  | 3.40           | 0.126 | 0.134 |

Millimeters

Dim.

